

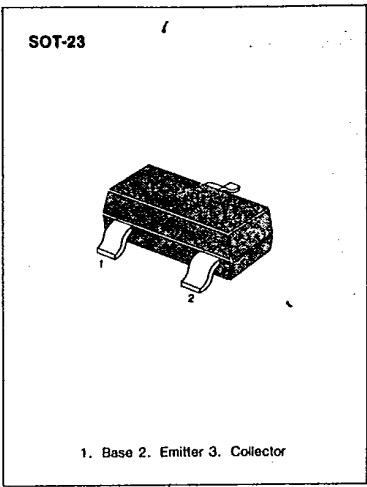
MMBC1622D6

NPN EPITAXIAL SILICON TRANSISTOR

AMPLIFIER TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

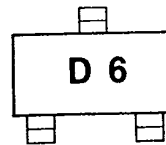
Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	40	V
Collector-Emitter Voltage	V _{CE0}	35	V
Emitter-Base Voltage	V _{EB0}	5.0	V
Collector Current	I _C	100	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{stg}	150	°C



ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I _{CB0}	V _{CB} = 25V, I _E = 0		50	nA
Emitter Cutoff Current	I _{EB0}	V _{EB} = 5V, I _C = 0		50	nA
DC Current Gain	h _{FE}	V _{CE} = 3V, I _C = 0.1mA	150		
		V _{CE} = 3V, I _C = 0.5mA	200	400	
Collector-Emitter Saturation Voltage	V _{CE (sat)}	I _C = 100mA, I _B = 10mA		0.3	V
Base-Emitter On Voltage	V _{BE (on)}	I _C = 0.5mA, V _{CE} = 3V	0.55	0.65	V
Current Gain-Bandwidth Product	f _T	V _{CE} = 6V, I _E = 1.0mA f = 100MHz	100		MHz

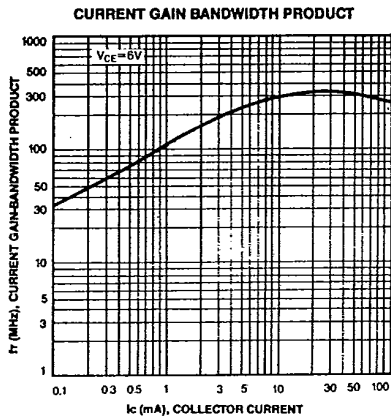
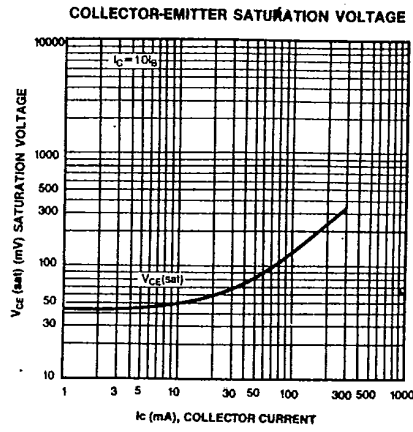
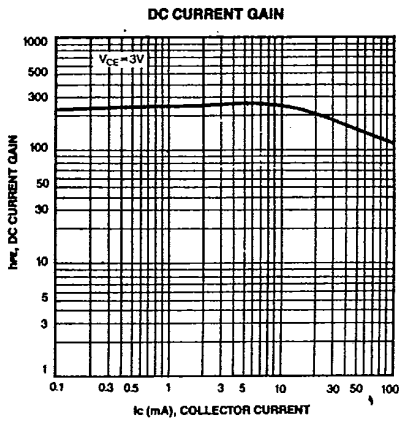
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T-29-19



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